

Silicon Carbide (SiC) Schottky Diode - EliteSiC, 10 A, 650 V, D1, DPAK

FFSD1065A

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and

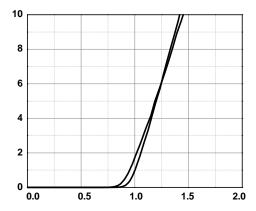
FFSD1065A

MAXIMUM RATINGS ($T_C = 25$			

FFSD1065A

TYPICAL CHARACTERISTICS

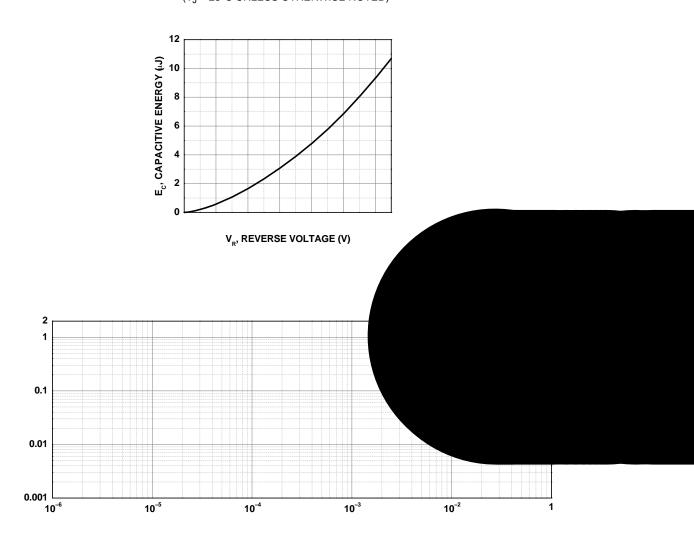
 $(T_J = 25^{\circ}C \text{ UNLESS OTHERWISE NOTED})$



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TYPICAL CHARACTERISTICS (CONTINUED)

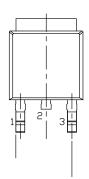
 $(T_J = 25^{\circ}C \text{ UNLESS OTHERWISE NOTED})$

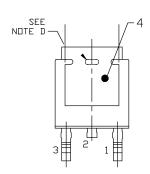


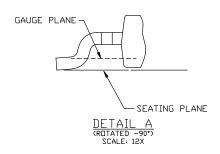


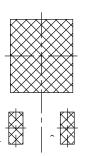
DPAK3 6.10x6.54x2.29, 4.57P CASE 369AS ISSUE B

DATE 20 DEC 2023









LAND PATTERN RECOMMENDATION

GENERIC MARKING DIAGRAM*

XXXXXX XXXXXX AYWWZZ

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

XXXX = Specific Device Code

A = Assembly Location Y = Year

Y = Year WW = Work Week

ZZ = Assembly Lot Code

